MicroCapacitance (MC) SA SIDACtor® Device







These DO-214AA SAMC SIDACtor devices are intended for applications sensitive to load values. Typically, high speed connections, such as Ethernet, xDSL, and T1/E1, require a lower capacitance. Co values for the MicroCapacitance device are 40% lower than a standard SA part.

This SAMC SIDACtor series enables equipment to comply with various regulatory requirements including GR 1089, ITU K.20, K.21, and K.45, IEC 60950, UL 60950, and TIA-968-A (formerly known as FCC Part 68).

Electrical Parameters

| Part Number * | V _{DRM} Volts | V _S Volts | V _T Volts | I _{DRM} μAmps | I _S mAmps | I _T Amps | I _H mAmps |
|------------------|---------------------------|-------------------------|-------------------------|---------------------------|-------------------------|------------------------|-------------------------|
| P0080SAMCL | 6 | 25 | 4 | 5 | 800 | 2.2 | 50 |
| P0220SAMCL | 15 | 32 | 4 | 5 | 800 | 2.2 | 50 |
| P0300SAMCL | 25 | 40 | 4 | 5 | 800 | 2.2 | 50 |

^{* &}quot;L" in part number indicates RoHS compliance. For non-RoHS compliant device, delete "L" from part number. For surge ratings, see table below.

General Notes:

- All measurements are made at an ambient temperature of 25 °C. I_{PP} applies to -40 °C through +85 °C temperature range.
- IPP is a repetitive surge rating and is guaranteed for the life of the product.
- · Listed SIDACtor devices are bi-directional. All electrical parameters and surge ratings apply to forward and reverse polarities.
- V_{DRM} is measured at I_{DRM}.
- V_S is measured at 100 V/µs.
- Special voltage (V_S and V_{DRM}) and holding current (I_H) requirements are available upon request.

Surge Ratings in Amps

| | lpp | | | | | | | | | | |
|--------|-------------------------|-------------------|---------------------|------|-----------------------|------|------|-------------------------|------|--------------------------------|---------|
| Series | 0.2x310 * 0.5x700 ** | 2x10 * 2x10 ** | 8x20 * 1.2x50 ** | | 10x560 * 10x560 ** | | | 10x1000 * 10x1000 ** | | I _{TSM} 50 / 60 Hz | di/dt |
| | Amps | Amps | Amps | Amps | Amps | Amps | Amps | Amps | Amps | Amps | Amps/µs |
| Α | 20 | 150 | 150 | 90 | 50 | 75 | 75 | 45 | 75 | 20 | 500 |

* Current waveform in μs
** Voltage waveform in μs



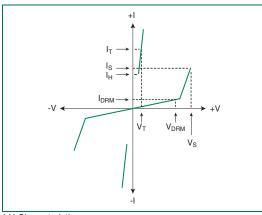
Thermal Considerations

| Package | Symbol | Parameter | Value | Unit |
|----------|-----------------|---|-------------|------|
| DO-214AA | T_J | Operating Junction Temperature Range | -40 to +150 | °C |
| | T _S | Storage Temperature Range | -65 to +150 | °C |
| | $R_{\theta JA}$ | Thermal Resistance: Junction to Ambient | 90 | °C/W |

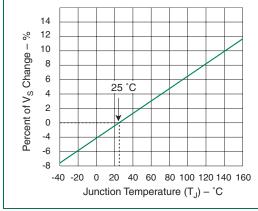
Capacitance Values

| | pF | | |
|-------------|-----|-----|--|
| Part Number | MIN | MAX | |
| P0080SAMCL | 25 | 55 | |
| P0220SAMCL | 25 | 50 | |
| P0300SAMCL | 15 | 35 | |

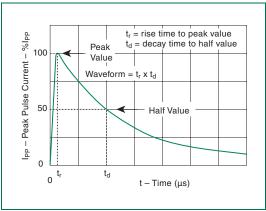
Note: Off-state capacitance (C_O) is measured at 1 MHz with a 2 V bias.



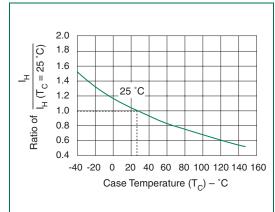
V-I Characteristics



Normalized V_S Change versus Junction Temperature



t_r x t_d Pulse Waveform



Normalized DC Holding Current versus Case Temperature